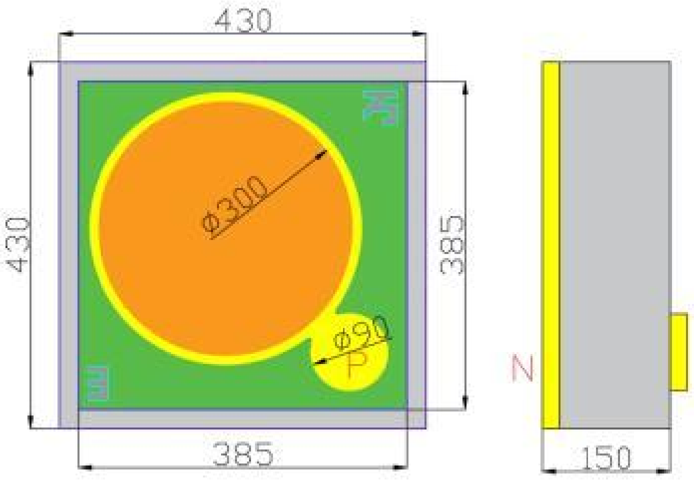
1740nm InGaAs 300um PD Chip datasheet

P/N ：WIR3-300



Feature

High responsivity

Low dark current

900-1740nm Spectral range

Structure

InGaAs / InP PIN Chip.

P Electrode (anode) : Gold.

N Electrode (cathode) : Gold.

DIMENSIONS

Conditions	Min.	Typ.	Max	Unit
Active	295	300	305	μm
Chip width	410	430	450	μm
Chip length	410	430	450	μm
Chip height	130	150	170	μm
Pad Area	85	90	95	μm

Electro-Optical Characteristics (@ Ta=25 ℃)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Dark current	Id	Vr=-5V	--	0.2	1	nA
Capacitance	Cp	Vr=-5V	-	7	10	pF
Reverse Breakdown	Vbr	Ir=-1μA	20	35	--	V
Responsivity	R	Vr=0V,@1654 nm	0.95	1	-	A/W
Wavelength range	λ		900	1650	1740	nm

ABSOLUTE MAXIMUM RATING

Parameter	Rating
Operating Temperature	-40℃ to 85℃
Storage Temperature	-55℃ to 125℃
Forward Current	10mA